
October 20 (Tue.), 2026

[Oral 01] CMP for Advanced Interconnects (I)

09:55-11:20

International Conference Hall (B1F)

● Session Chair: Patrick Ong (imec, Belgium)

09:55-10:20 **[Invited]** CMP Process Innovations, Growing Needs and Challenges Imposed
[Oral 01-1] by New Architectures, New Materials and Dimensional Scaling for Logic and
Advanced Interconnects

Nancy Heylen (imec, Belgium)

10:20-10:40 Research on CMP Slurry for Removal Rate and Defect Control for Sub-10nm
[Oral 01-2] Node Semiconductors

Jong-Young Cho (SK hynix Inc., Korea), Deok-Su Han (YCCChem Co., Ltd., Korea), Woojoo Kim (SK hynix Inc., Korea), and Hyun-goo Kang (SK hynix Inc., Korea)

10:40-11:00 Advanced Tungsten Slurry with Low Etching Rate, High W / Oxide Selectivity,
[Oral 01-3] and E-O-E Free Topography

Sanghwan Kim, Guo Yi (Qnity Electronics, Inc., USA), Joseph Sung, and Allison Hsu (Qnity Electronics, Inc., Taiwan)

11:00-11:20 Innovative Solution for High Throughput Density Tungsten CMP Through In-
[Oral 01-4] situ Conditioning Development

Zhengqiu Sun, Wern Jun Mak (Micron SemiAsiaOP Pte Ltd, Singapore), and Arvin Chang (Micron Memory Taiwan Co., Taiwan)